# TFD-3G12-100

## 1310 nm High Power FP LD

## **Features and Applications**

- 1310 nm emission wavelength
- Capable to run 1.25G bps and above data rate

## ELECTRO-OPTICAL CHARACTERISTICS:

ELECTRO-OFFICAL CHARACTERISTICS.									
PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS			
Operating Wavelength	$\lambda_{\mathrm{P}}$	1290	1310	1330	nm	Power = 5mW			
Threshold Current	Ith		10	13	mA				
Slope Efficiency	$\eta$	0.42	0.49		mW/mA	Power = $1-5 \text{ mW}$			
Operating Voltage	$V_{op}$		1.2	1.5	V	Power = 5mW			
Series Resistance	Rs		8	12	Ohm	Power = $1-5 \text{ mW}$			
Spectrum wavelength	Δλ		2	3	nm	Power = 5mW			
Divergence angle ( Parallel ) Divergence angle ( Perpendicular )	θ//		18		degree				
	$\theta \perp$		35		degree				

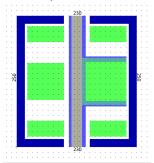
Notes: All parameters are measured at 25°C room temperature, CW operation.

### **ABSOLUTE MAXIMUM RATINGS:**

PARAMETERS	MIN	MAX	UNIT	CONDITION
Storage Temperature	-40	85	°C	
Operating Temperature	-40	85	°C	
Output power		10	mW	
Reverse Voltage		2	V	

### **OUTLINE DIAGRAM:**

• chip size is 230 x 250  $\mu m$  with 100+/-15um thickness.



### **WARNING:**

The FP LD is a class 3B laser in the safety standard IEC60825-1:2014 and should be treated to avoid exposure to beam

